

1774
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Re Application of:

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5A
95-01
Art unit: 1774

Serial No. 09/547,415

Examiner: D. GARRETT

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For: FULL COLOR DISPLAY STRUCTURE USING CNC THIN FILM

PRRELIMINARY AMENDMENT (clear copy)

Commissioner of Patents
Washington, D.C. 20231

Sir:

Please amend the original patent application as follows:

IN THE CLAIMS:

Please rewrite claim 2 as follows:

A1
--2. An EL device of claim 1, wherein the thin wide energy gap semiconductor layer over the said CNC layer is undoped.--

Please delete claim 4.

Please amend claim 5 as follows:

113
3A2
22
--5. An EL device of claim 1, wherein said CNC layer is sandwiched between compatible wide energy gap semiconductor layers selected from the group of semiconductors consisting of $\text{Zn}_a\text{Mg}_{1-a}\text{Se}$, $\text{Zn}_a\text{Mg}_{1-a}\text{S}$, $\text{Zn}_a\text{Mg}_{1-a}\text{SbSe}_{1-b}$, $\text{Zn}_a\text{Be}_{1-a}\text{SbSe}_{1-b}$, $\text{AlcGa}_{1-c}\text{N}$, and AlInN .--

Please amend claim 8 as follows:

A3
1135
--8. An EL device of claim 1, wherein the layer comprising CNC further comprises multiple layers of CNCs sandwiched between epitaxially grown thin film layers of wide energy gap semiconductors. --

Please cancel claims 9.

Please rewrite claim 11 as follows:

A4
--11. An device EL device as described in claim 1, wherein said first p-doped Si layer is substituted by a transparent ITO, forming the bottom electrodes.--

Please rewrite claims 13-16 as follows:

115
--13. An EL device of claim 1, wherein the p-doped wide energy gap semiconductor layer underneath the said CNC layer is replaced by a dielectric layer.

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